



SOT-23 Plastic-Encapsulate Transistors

MMBTA05 TRANSISTOR (NPN)

FEATURES

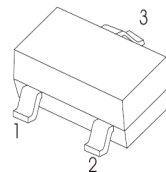
Driver transistor

MARKING :1H

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current -Continuous	0.5	A
P _C	Collector Power Dissipation	300	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =60V, I _B =0			0.1	μA
Collector cut-off current	I _{EBO}	V _{EB} =3V, I _C =0			0.1	μA
DC current gain	h _{FE1}	V _{CE} =1V, I _C = 10mA	100		400	
	h _{FE2}	V _{CE} =1V, I _C = 100mA	100			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.25	V
Base-emitter voltage	V _{BE}	V _{CE} =1V, I _C = 100mA			1.2	V
Transition frequency	f _T	V _{CE} = 2V, I _C =10mA f=100MHz	100			MHz

Typical Characteristics

MMBTA05

